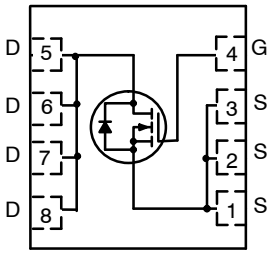
MOSFET – N-Channel, DUAL COOL® 33, POWERTRENCH®

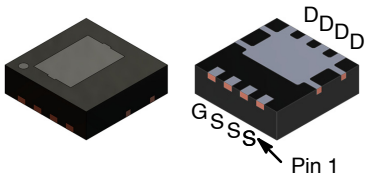
30 V, 40 A, 2.2 mΩ

FDMC7660DC

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30 V	2.2 mΩ @ 10 V	40 A
	3.3 mΩ @ 4.5 V	



N-CHANNEL MOSFET



PQFN8 3.3 × 3.3, 0.65P
(DUAL COOL 33)
CASE 483AL

General Description

This N−Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process. Advancements in both silicon and DUAL COOL package technologies have been combined to offer the lowest $R_{DS(on)}$ while maintaining excellent switching performance by extremely low Junction−to−Ambient thermal resistance.

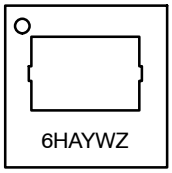
Features

- DUAL COOL Top Side Cooling PQFN Package
- Max $R_{DS(on)}$ = 2.2 mΩ at V_{GS} = 10 V, I_D = 22A
- Max $R_{DS(on)}$ = 3.3 mΩ at V_{GS} = 4.5 V, I_D = 18 A
- High Performance Technology for Extremely Low $R_{DS(on)}$
- SyncFET™ Schottky Body Diode
- Pb−Free, Halide Free and RoHS Compliant

Applications

- Synchronous Rectifier for DC/DC Converters
- Telecom Secondary Side Rectification
- High End Server/Workstation

MARKING DIAGRAM



6H = Specific Device Code
A = Assembly Plant Code
YW = Date Code (Year and Week)
Z = Lot Code

ORDERING INFORMATION

Device	Package	Shipping†
FDMC7660DC	PQFN8 (Pb−Free, Halide Free)	3000 / Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MOSFET MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter			Value	Unit
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage (Note 4)			±20	V
I_D	Drain Current	Continuous (Package limited)	T_C = 25°C	40	A
		Continuous (Silicon limited)	T_C = 25°C	150	
		Continuous (Note 1a)	T_A = 25°C	30	
		Pulsed		200	
E_{AS}	Single Pulse Avalanche Energy (Note 3)			220	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 5)			1.0	V/ns
P_D	Power Dissipation		T_C = 25°C	78	W
	Power Dissipation (Note 1a)		T_A = 25°C	3.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case (Top Source)	4.3	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case (Bottom Drain)	1.6	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1a)	42	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1b)	105	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1i)	17	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1j)	26	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1k)	12	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	30	–	–	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	15	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V	–	–	100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.2	2	2.5	V
$\Delta V_{GS(th)}$ / ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C	–	−7	–	mV/°C
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 22 A	–	1.6	2.2	mΩ
		V_{GS} = 4.5 V, I_D = 18 A	–	2.5	3.3	
		V_{GS} = 10 V, I_D = 22 A, T_J = 125°C	–	2.2	3.3	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 22 A	–	147	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	–	3885	5170	pF
C_{oss}	Output Capacitance		–	1215	1620	pF
C_{rss}	Reverse Transfer Capacitance		–	100	150	pF
R_g	Gate Resistance		–	0.7	1.5	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn−On Delay Time	V_{DD} = 15 V, I_D = 22 A, V_{GS} = 10 V, R_{GEN} = 6 Ω	–	17	31	ns
t_r	Rise Time		–	6.6	13	ns
$t_{d(off)}$	Turn−Off Delay Time		–	36	58	ns
t_f	Fall Time		–	5	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V, V_{DD} = 15 V, I_D = 22 A	–	54	76	nC
		V_{GS} = 0 V to 4.5 V, V_{DD} = 15 V, I_D = 22 A	–	24	34	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 15 V, I_D = 22 A	–	13	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	5.5	–	nC
DRAIN−SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source−Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 22 A (Note 2)	–	0.8	1.2	V
		V_{GS} = 0 V, I_S = 1.9 A (Note 2)	–	0.7	1.2	
t_{rr}	Reverse Recovery Time	I_F = 22 A, di/dt = 100 A/μs	–	43	69	ns
Q_{rr}	Reverse Recovery Charge		–	24	38	nC

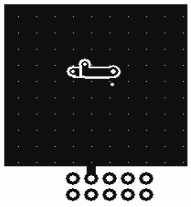
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

THERMAL CHARACTERISTICS

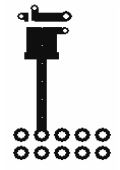
Symbol	Characteristic	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case (Top Source)	4.3	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case (Bottom Drain)	1.6	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1a)	42	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1b)	105	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1c)	29	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1d)	40	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1e)	19	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1f)	23	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1g)	30	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1h)	79	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1i)	17	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1j)	26	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1k)	12	
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient (Note 1l)	16	

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a FR−4 board using a specified pad of 2 oz copper as shown below. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 42°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b) 105°C/W when mounted on a minimum pad of 2 oz copper.

c) Still air, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, 1 in^2 pad of 2 oz copper
d) Still air, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, minimum pad of 2 oz copper
e) Still air, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10−L41B−11 Heat Sink, 1 in^2 pad of 2 oz copper
f) Still air, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10−L41B−11 Heat Sink, minimum pad of 2 oz copper
g) 200FPM Airflow, No Heat Sink,1 in^2 pad of 2 oz copper
h) 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper
i) 200FPM Airflow, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, 1 in^2 pad of 2 oz copper
j) 200FPM Airflow, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, minimum pad of 2 oz copper
k) 200FPM Airflow, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10−L41B−11 Heat Sink, 1 in^2 pad of 2 oz copper
l) 200FPM Airflow, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10−L41B−11 Heat Sink, minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 220 mJ is based on starting T_J = 25°C, N−ch: L = 1 mH, I_{AS} = 21 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% test at L = 0.3 mH, I_{AS} = 33.5 A.
4. As an N−ch device, the negative Vgs rating is for low duty cycle pulse ocurrence only. No continuous rating is implied.
5. $I_{SD} \le 22$ A, di/dt ≤ 100 A/μs, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C.

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

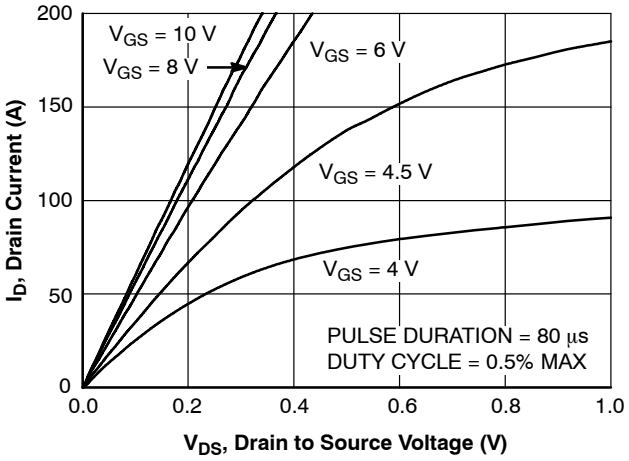


Figure 1. On−Region Characteristics

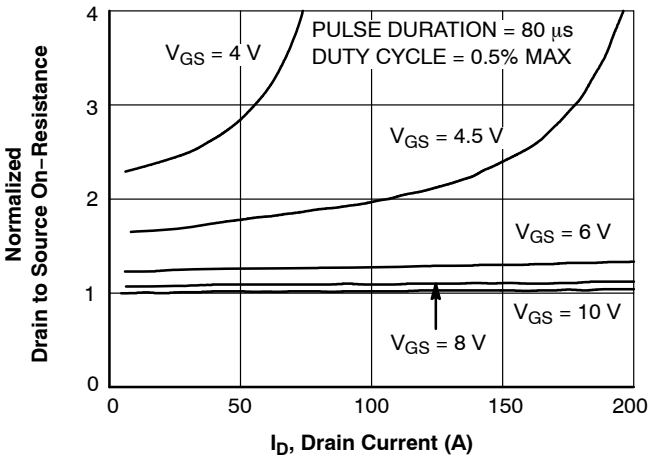


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

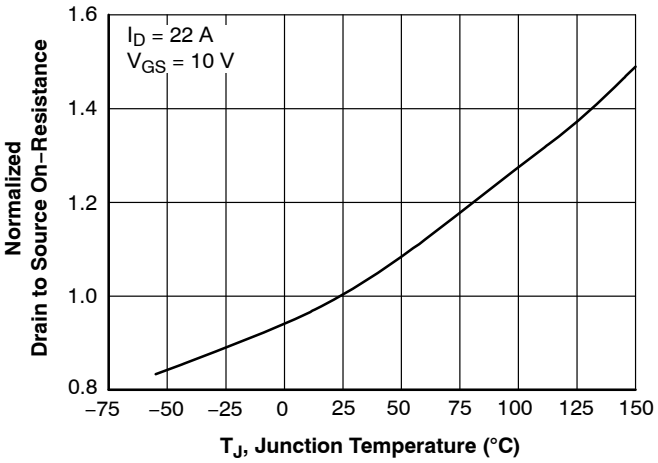


Figure 3. Normalized On−Resistance vs. Junction Temperature

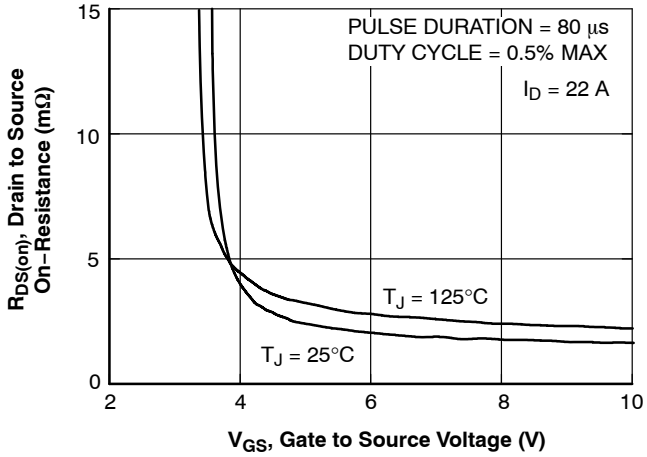


Figure 4. On−Resistance vs. Gate to Source Voltage

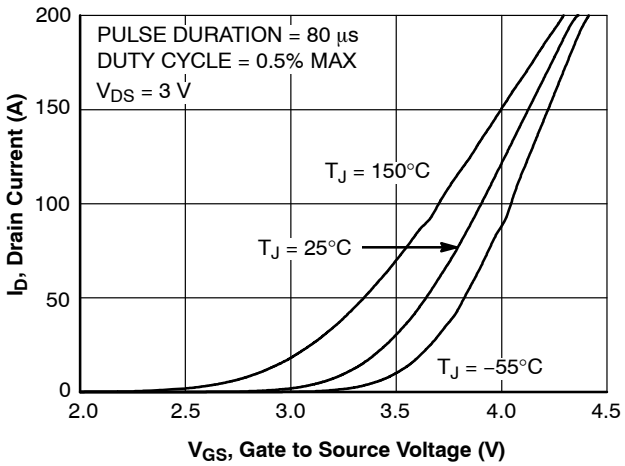


Figure 5. Transfer Characteristics

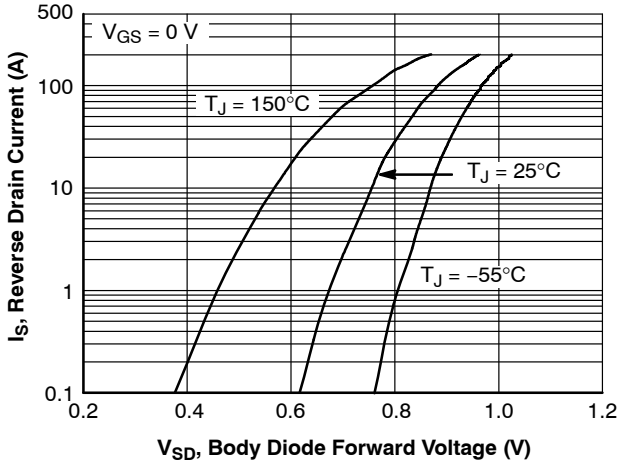


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

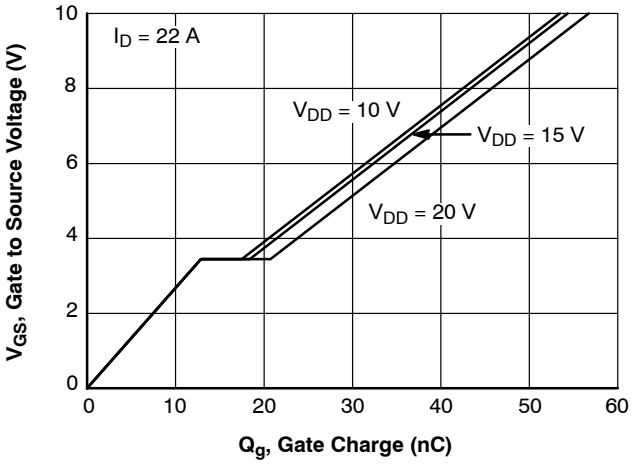


Figure 7. Gate Charge Characteristics

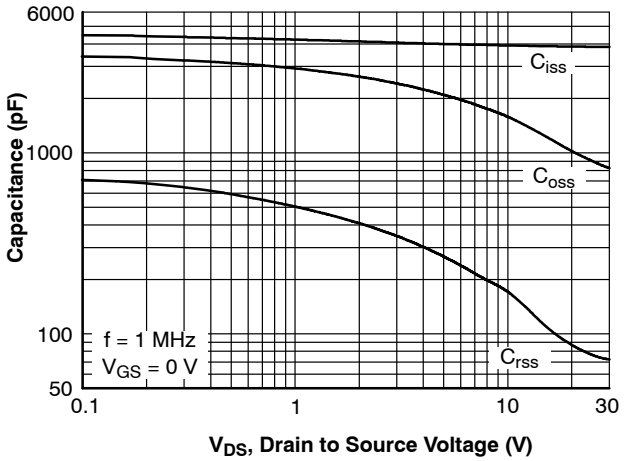


Figure 8. Capacitance vs. Drain to Source Voltage

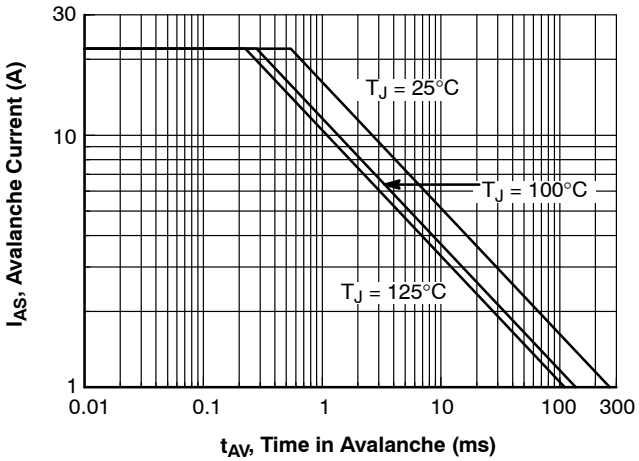


Figure 9. Unclamped Inductive Switching Capability

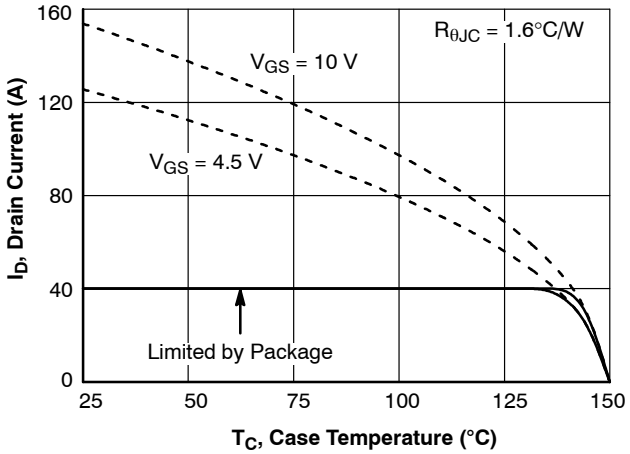


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

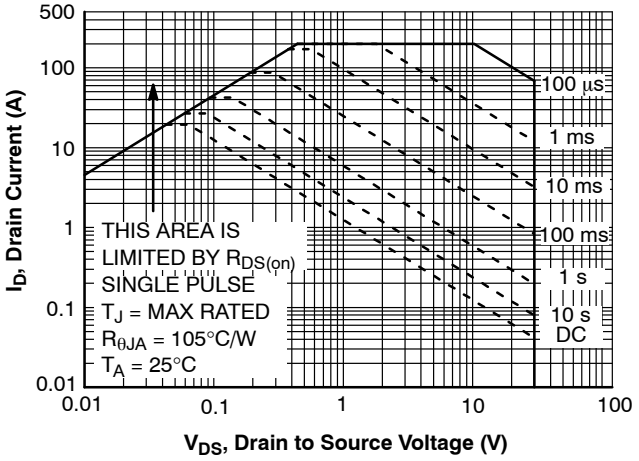


Figure 11. Forward Bias Safe Operating Area

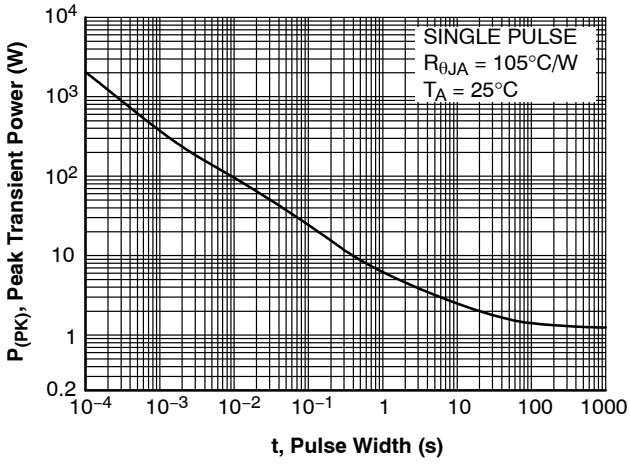


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

(T_J = 25°C unless otherwise noted)

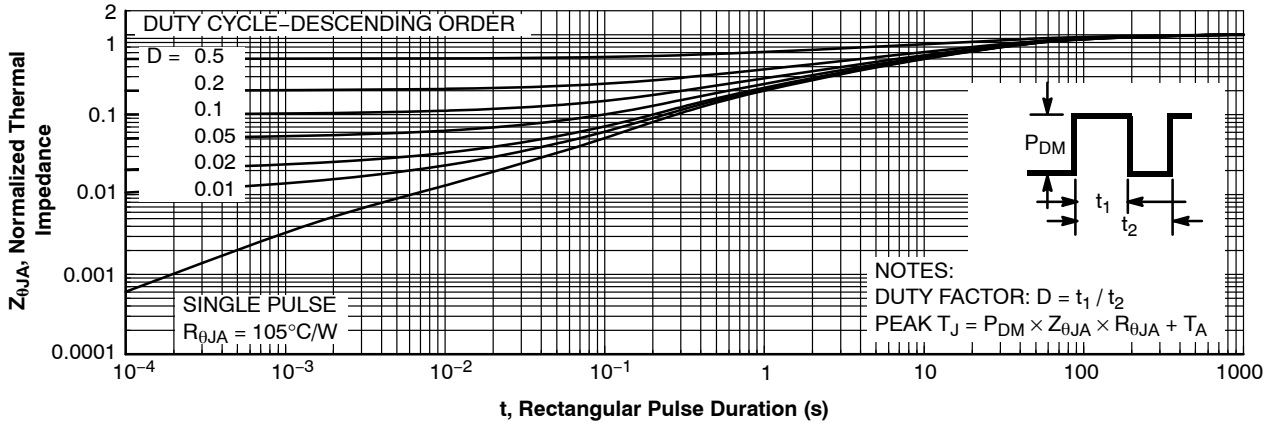
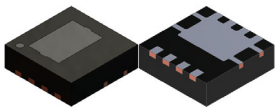
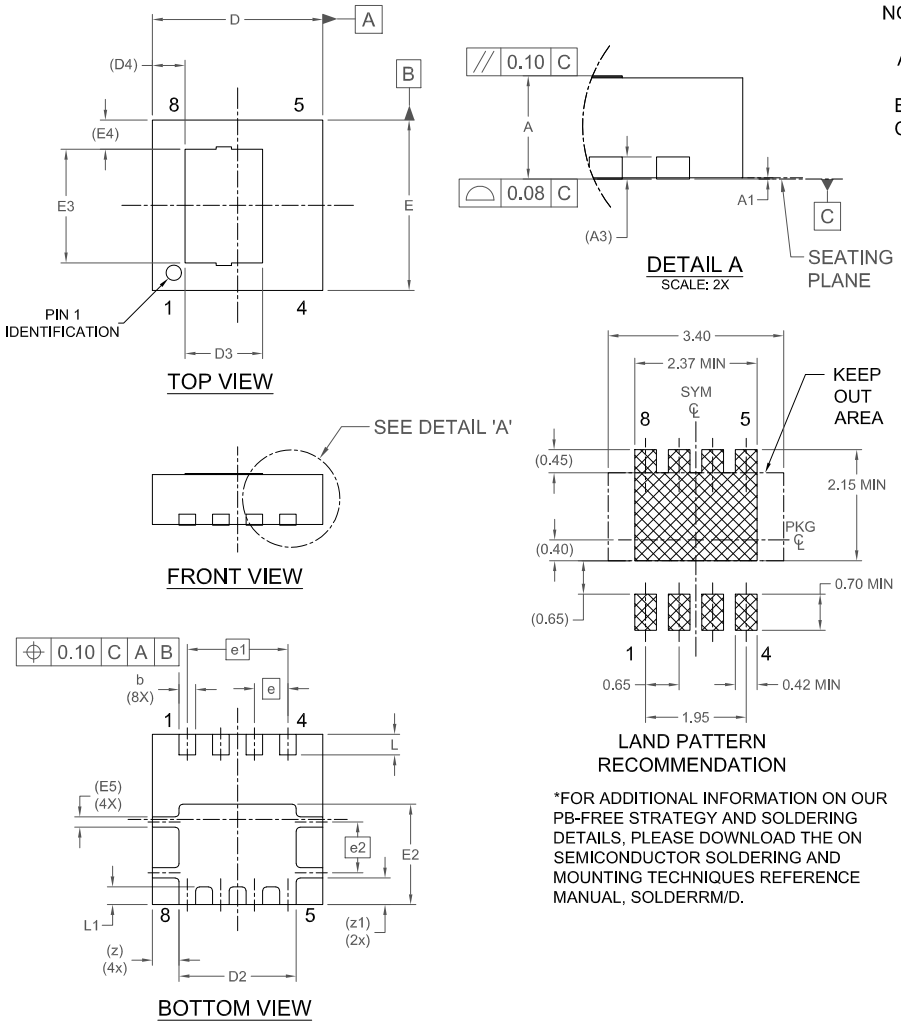


Figure 13. Junction−to−Ambient Transient Thermal Response Curve



PQFN8 3.30x3.30x1.00, 0.65P
CASE 483AL
ISSUE B

DATE 20 DEC 2023



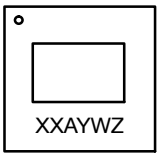
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

A. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.27	0.32	0.37
A3		0.20 REF	
D	3.20	3.30	3.40
D2	2.17	2.27	2.37
D3	1.40	1.55	1.70
D4		0.63 REF	
E	3.20	3.30	3.40
E2	1.90	2.00	2.10
E3	2.10	2.25	2.40
E4		0.56 REF	
E5		0.20 REF	
e		0.65 BSC	
e1		1.95 BSC	
e2		0.98 BSC	
L	0.30	0.40	0.50
L4	0.29	0.39	0.49
z		0.52 REF	
z1		0.52 REF	

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
Z = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON13661G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**PQFN8 3.30x3.30x1.00, 0.65P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

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